

ATTY DOCKET NO.
03500.013395.2APPLICATION NO.
Div. of 09/839,891

APPLICANT

KEISHI SAITO ET AL.

FILING DATE

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GROUP

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U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
/	4,600,801	7/15/86	Guha et al.	136	249	
	4,609,771	9/2/86	Guha et al.	136	249	
	4,775,425	10/4/88	Guha et al.	136	249	
	5,486,237	1/23/96	Sano et al.	136	258	
	5,720,827	2/24/98	Simmons	136	250	
	5,851,904	12/22/98	Schwarz et al.	438	482	
	5,913,986	6/22/99	Matsuyama	136	255	
/9	6,013,544	1/11/00	Makita et al.	438	166	

FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO/ OR ABSTRACT
0 675 551	10/4/95	Europe			
43 33 416	4/6/95	Germany			

OTHER DOCUMENT(S) (Including Author, Title, Date, Pertinent Pages, Etc.)

J. Meier, et al., "Towards High Efficiency Thin Film Silicon Solar Cells With The 'Micromorph' Concept", Solar Energy Materials and Solar Cells, vol. 49, pp. 35-44 (1997).
J. Yi, et al., "Amorphous and Micro-Crystalline Silicon for Photovoltaic Application", Proc. of the Photovoltaic Spec. Conf., vol. 23, pp. 977-980 (1993).
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EXAMINER

DATE CONSIDERED

3/18/05

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO 1449 (modified) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE LIST OF REFERENCES CITED BY APPLICANT(S) (Use several sheets if necessary)			ATTY DOCKET NO. 03500.013395.2	APPLICATION NO. Div. of 09/839,891	Cont'd	
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	6,020,224	2/1/00	Shimogaichi et al.	438	158	
	6,027,987	2/22/00	Yamazaki et al.	438	486	
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	1175095A	3/4/98	China			
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